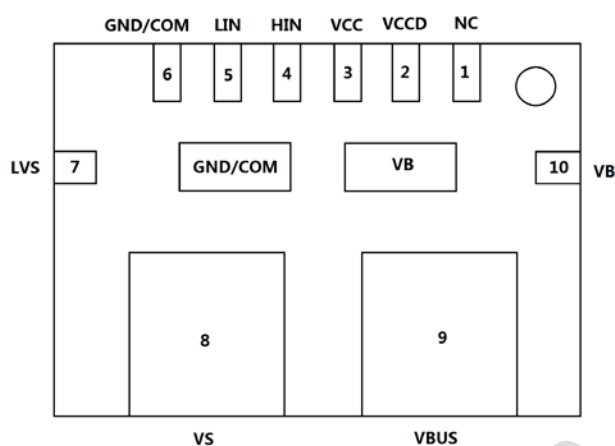


管脚封装



FG4311 管脚封装图

管脚描述

管脚号	管脚名称	类型	管脚描述
1		NC	
2	VCCD	P	内置二极管输入端
3	VCC	P	电源供电输入脚
4	HIN	I	高侧输入
5	LIN	I	低侧输入
6	GND/COM	P	地
7	LVS	O	低侧输出
8	VS	O	高侧输出
9	VBUS	I	直流电压输入端
10	VB	I	高侧驱动供电

订购信息

产品名称	封装类型	数量	产品包装
FG4311	DFN5X6-10L	XXXX	XXXX

MOSFET Electrical Characteristic (T_A=25°C)

SYMBOL	CHARACTERISTIC	TEST CONDITION	MIN	TYP	MAX	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0V, I _D = 250 uA	500			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{GS} = 0V, V _{DS} = 500V			1	uA
V _{GS(TH)}	Gate Threshold Voltage	V _{GS} = V _{DS} , I _D = 250 uA	2	3	4	V
I _{GSS}	Gate Leakage Current	V _{DS} = 0V, V _{GS} = ±32V			±100	nA
R _{DS(ON)}	Drain-to-Source ON-resistance	V _{GS} = 10V, I _D = 1.5A		2.4	3	Ω

MOSFET Absolute Maximum Rating (T_A=25°C)

SYMBOL	Parameter	Value	UNIT
V _{DSS}	Drain-Source Voltage	500	V
V _{GSS}	Gate-Source Voltage	±30	V
I _D	Continue Drain Current	5	A
T _J	Operation Junction Temperature Range	-55 to 150	°C
T _{STG}	Storage Temperature Range	-55 to 150	°C

DIODE Maximum Ratings

SYMBOL	CHARACTERISTIC	RATING	UNIT
V _{RRM}	Repetitive peak reverse voltage	500	V
I _{F(AV)}	Average forward current	0.5	A
T _{STG}	Storage temperature range	-50 to +140	°C
T _J	Maximum operating junction temperature	140	°C

DIODE Static Electrical Characteristics (T_a = 25°C)

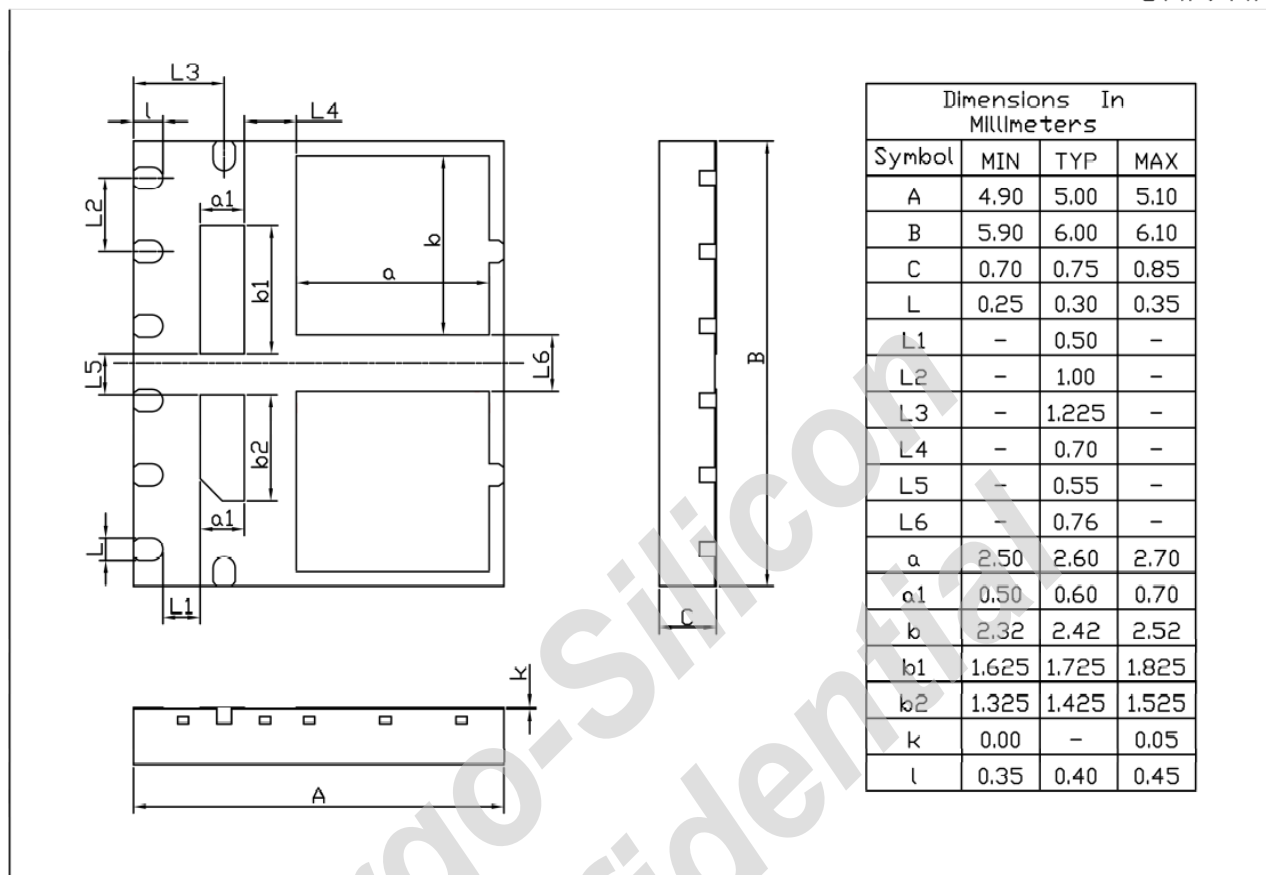
SYMBOL	Parameter	MIN	MAX	UNIT
V _{BR}	Reverse breakdown voltage I _R = 5uA	500	/	V
V _F	Maximum forward voltage drop I _F = 0.2A	/	1.60	V
	Maximum forward voltage drop I _F = 0.5A	/	1.80	V
T _{rr}	Reverse Recovery time I _F =0.5A I _R =1A I _{RR} =0.25A	/	35	ns
I _R	Maximum reverse current V _R = V _{RRM}	/	1.0	uA

封装信息

DFN5×6-10L 外形尺寸图

DFN5×6-10L

Unit:mm



Rev.00 202304

版本信息

日期	版本	记录
2023.12.11	V1.0	初稿

联系方式

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